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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD2337

Silicon NPN Triple Diffused

RENESAS

ADE-208-929 (Z)
1st. Edition
September 2000

Application

Low frequency high voltage power amplifier TV vertical deflection output complementary pair with 2SB1530

Outline

TO-220FM



1. Base
2. Collector
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage | V_{CBO} | 200 | V |
| Collector to emitter voltage | V_{CEO} | 150 | V |
| Emitter to base voltage | V_{EBO} | 6 | V |
| Collector current | I_C | 2 | A |
| Collector peak current | $I_{C(peak)}$ | 5 | A |
| Collector power dissipation | P_C | 1.5 | W |
| | P_C^{*1} | 20 | |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -45 to +150 | °C |

Note: 1. Value at $T_C = 25^\circ\text{C}$.

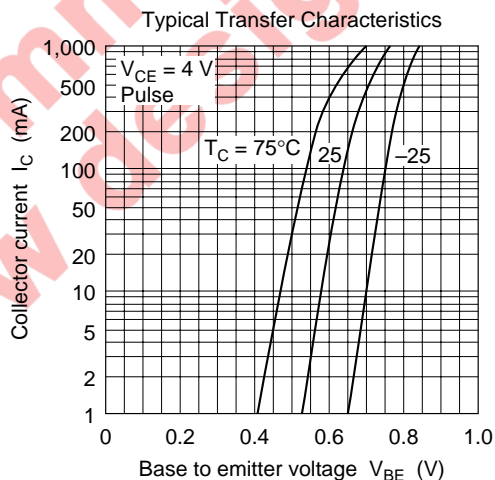
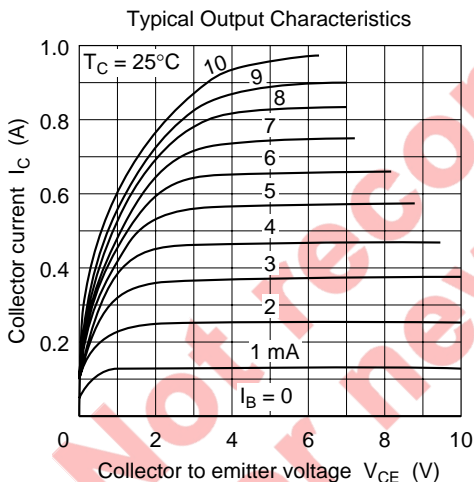
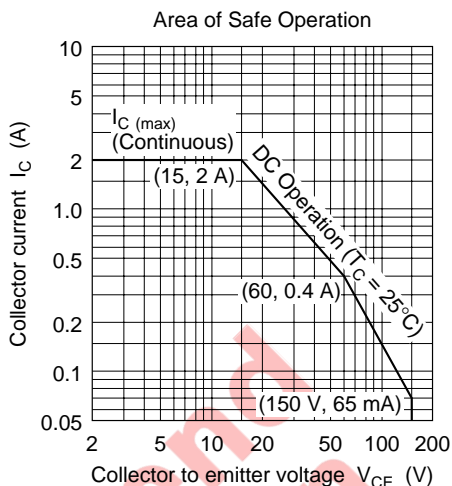
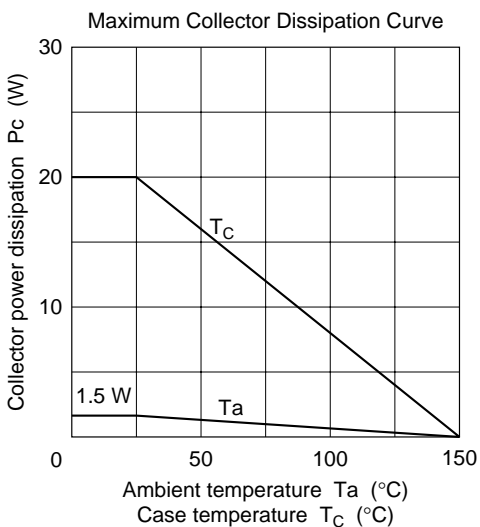
Electrical Characteristics (Ta = 25°C)

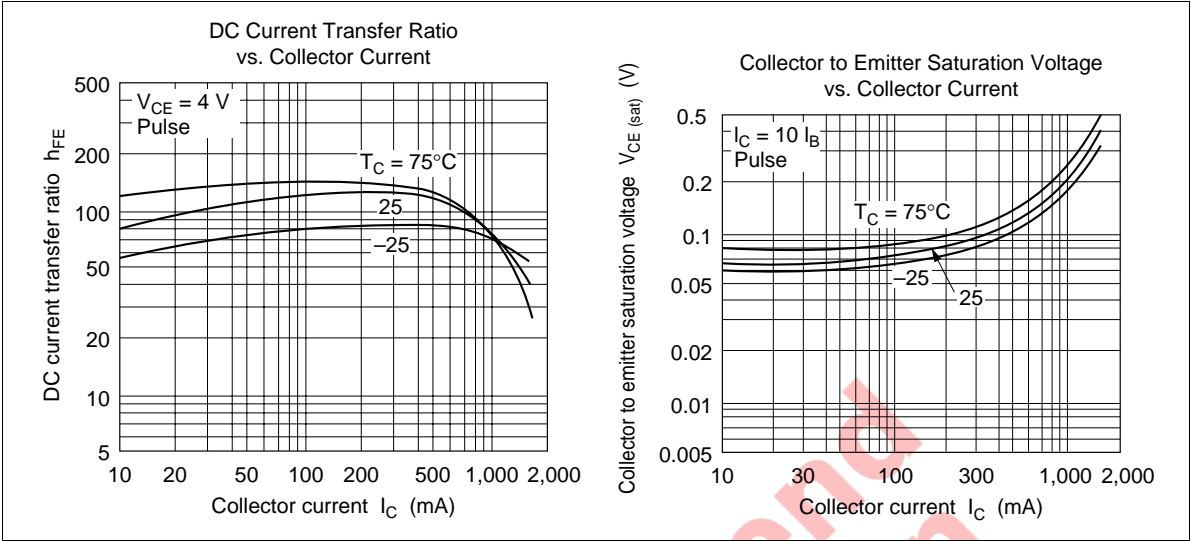
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|----------------|-----|-----|-----|---------------|---|
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 150 | — | — | V | $I_C = 50\text{ mA}$, $R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 6 | — | — | V | $I_E = 5\text{ mA}$, $I_C = 0$ |
| Collector cutoff current | I_{CBO} | — | — | 1 | μA | $V_{CB} = 120\text{ V}$, $I_E = 0$ |
| DC current transfer ratio | h_{FE1}^{*1} | 60 | — | 320 | | $V_{CE} = 4\text{ V}$, $I_C = 50\text{ mA}$ |
| | h_{FE2} | 60 | — | — | | $V_{CE} = 10\text{ V}$, $I_C = 500\text{ mA}^{*2}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | — | 3.0 | V | $I_C = 500\text{ mA}$, $I_B = 50\text{ mA}^{*2}$ |
| Base to emitter voltage | V_{BE} | — | — | 1.0 | V | $V_{CE} = 4\text{ V}$, $I_C = 50\text{ mA}$ |

Notes: 1. The 2SD2337 is grouped by h_{FE1} as follows.

2. Pulse test.

| B | C | D |
|-----------|------------|------------|
| 60 to 120 | 100 to 200 | 160 to 320 |





Not recommended for new design

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